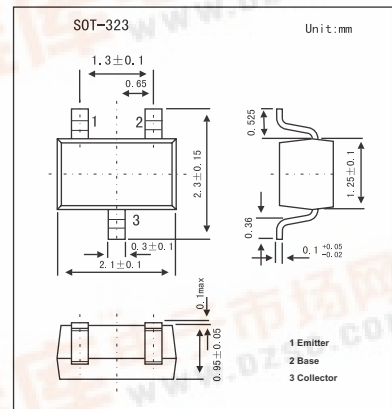


SMD Type Transistors

Medium Power Transistor
2SD1949

■ Features

- High current. (Ic=5A)
- Low saturation voltage, typically VCE(sat)=0.1V at Ic / Ib=150mA / 15mA.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _c	0.5	A
Collector power dissipation	P _c	0.2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV _{CB0}	I _c =1mA	50			V
Collector-emitter breakdown voltage	BV _{CEO}	V _{CB} =30V	50			V
Emitter-base breakdown voltage	BV _{EB0}	V _{EB} =4V	5			V
Collector cutoff current	I _{cBO}	V _{CE} /I _c =3V/0.01A			0.5	μA
Emitter cutoff current	I _{EBO}	V _{CE} =5V, I _E =-20mA, f=100MHz			0.5	μA
DC current transfer ratio	h _{FE}	V _{CB} =10V, I _E =0A, f=1MHz	120		390	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =100μA			0.4	V
Output capacitance	f _t	I _E =100μA		250		MHz
Transition frequency	C _{ob}	I _c /I _b =150mA/15mA		6.5		pF

■ hFE Classification

Marking	Y	
	Q	R
hFE	120~270	180~390

